

setting said substrate onto a stage having a surface roughness of 5 μm or less in such a manner that a lower surface of said substrate is in contact with said stage;

flattening said substrate by vacuum-sucking said lower surface of said substrate; and

Hand
irradiating said semiconductor film with a laser beam having a cross section which is elongated in one direction while relatively moving said substrate with respect to said laser beam, and while vacuum-sucking said lower surface of said substrate.

10. (Amended) A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film over an upper surface of a substrate;

Hand
setting said substrate onto a stage having a surface roughness of 5 μm or less and at least one suction inlet in such a manner that a lower surface of said substrate is in contact with said stage;

flattening said substrate by vacuum-sucking said lower surface of said substrate; and

irradiating said semiconductor film with a laser beam having a cross section which is elongated in one direction while relatively moving said substrate with respect to said laser

12298 beam, and while vacuum-sucking said lower surface of said substrate.

13. (Amended) A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film over a lower surface of a substrate;

heating said semiconductor film;

143 setting said substrate onto a stage having a surface roughness of 5 μm or less in such a manner that a lower surface of said substrate is in contact with said stage;

flattening said substrate by vacuum-sucking said lower surface of said substrate; and

irradiating said semiconductor film with a laser beam having a cross section which is elongated in one direction while relatively moving said substrate with respect to said laser beam, and while vacuum-sucking said lower surface of said substrate.

144 16. (Amended) A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film over an upper surface of a substrate;

heating said semiconductor film;

setting said substrate onto a stage having a surface roughness of 5 μm or less and at least one suction inlet in such a manner that a lower surface of said substrate is in contact with said stage;

Amended
flattening said substrate by vacuum-sucking said lower surface of said substrate; and

irradiating said semiconductor film with a laser beam having a cross section which is elongated in one direction while relatively moving said substrate with respect to said laser beam, and while vacuum-sucking said lower surface of said substrate.

19. (Amended) A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film over an upper surface of a substrate;

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heating said substrate to crystallize said semiconductor film;

setting said substrate onto a stage having a surface roughness of 5 μm or less in such a manner that a lower surface of said substrate is in contact with said stage;

flattening said substrate by vacuum-sucking said lower surface of said substrate; and

Here
irradiating the crystallized semiconductor film over said substrate provided on said stage with a laser beam having a cross section which is elongated in one direction while relatively moving said substrate with respect to said laser beam, and while vacuum-sucking said lower surface of said substrate.

22. (Amended) A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film over an upper surface of a substrate;

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heating said substrate to crystallize said semiconductor film;

setting said substrate onto a stage having a surface roughness of 5 μm or less and at least one suction inlet in such a manner that a lower surface of said substrate is in contact with said stage;

flattening said substrate by vacuum-sucking said lower surface of said substrate; and

irradiating the crystallized semiconductor film with a laser beam having a cross section which is elongated in one direction while relatively moving said substrate with respect to said laser beam, and while vacuum-sucking said lower surface of said substrate.

51. (Amended) A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film over an upper surface of a substrate;

setting said substrate onto a stage having a surface roughness of 5 μm or less in such a manner that a lower surface of said substrate is in contact with said stage;

flattening said substrate by vacuum-sucking said lower surface of said substrate; and

irradiating said semiconductor film with a laser beam while relatively moving said substrate with respect to said laser beam, and while vacuum-sucking said lower surface of said substrate.

56. (Amended) A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film over an upper surface of a substrate;

heating said semiconductor film;

setting said substrate onto a stage having a surface roughness of 5 μm or less in such a manner that a lower surface of said substrate is in contact with said stage;

flattening said substrate by vacuum-sucking said lower surface of said substrate; and

irradiating said semiconductor film with a laser beam while
relatively moving said substrate with respect to said laser
beam, and while vacuum-sucking said lower surface of said
substrate.
